

Electronic supplementary materials

**Aqueous Phase Fabrication and Conversion of Pb(OH)Br into CH<sub>3</sub>NH<sub>3</sub>PbBr<sub>3</sub> Perovskite and its Application in Resistive Memory Switching Devices**

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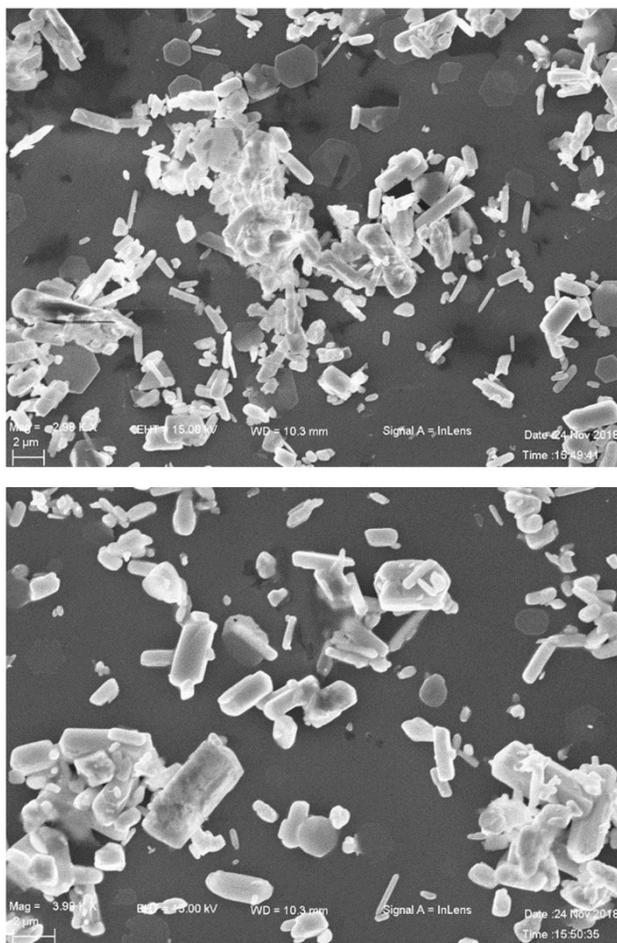
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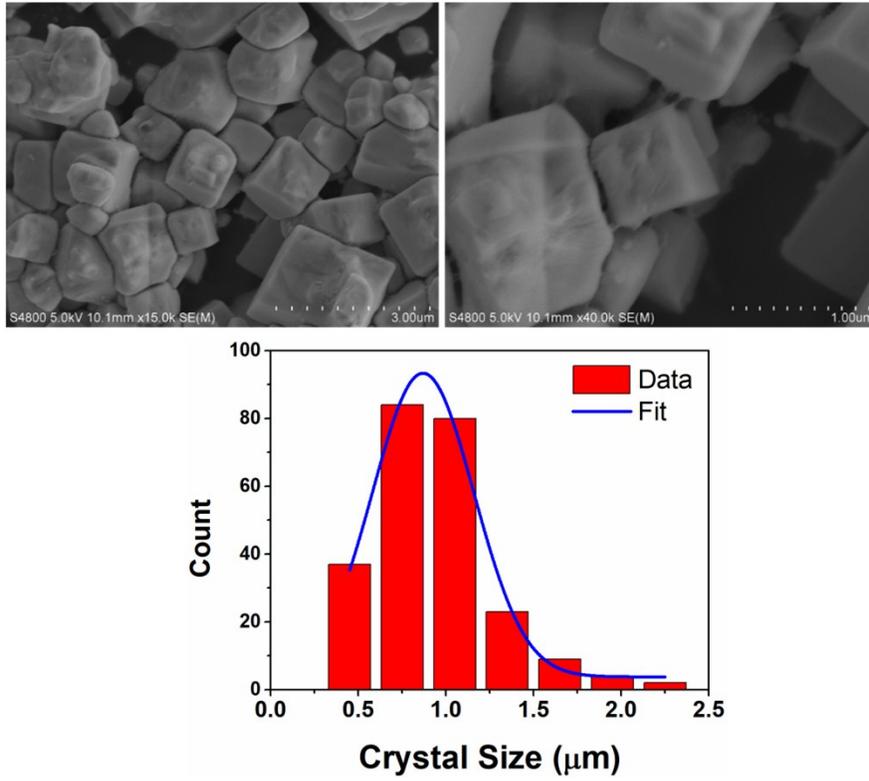
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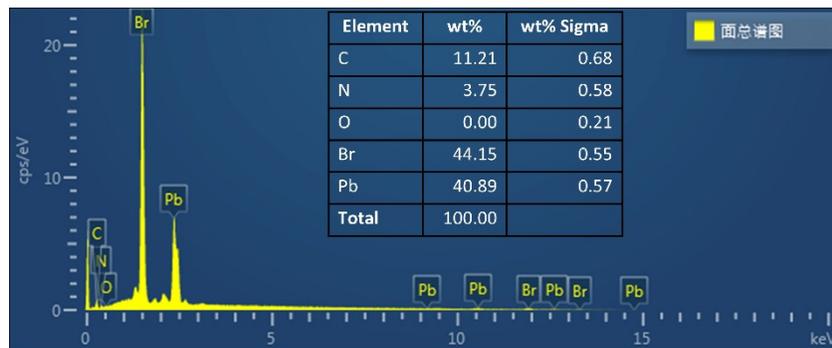
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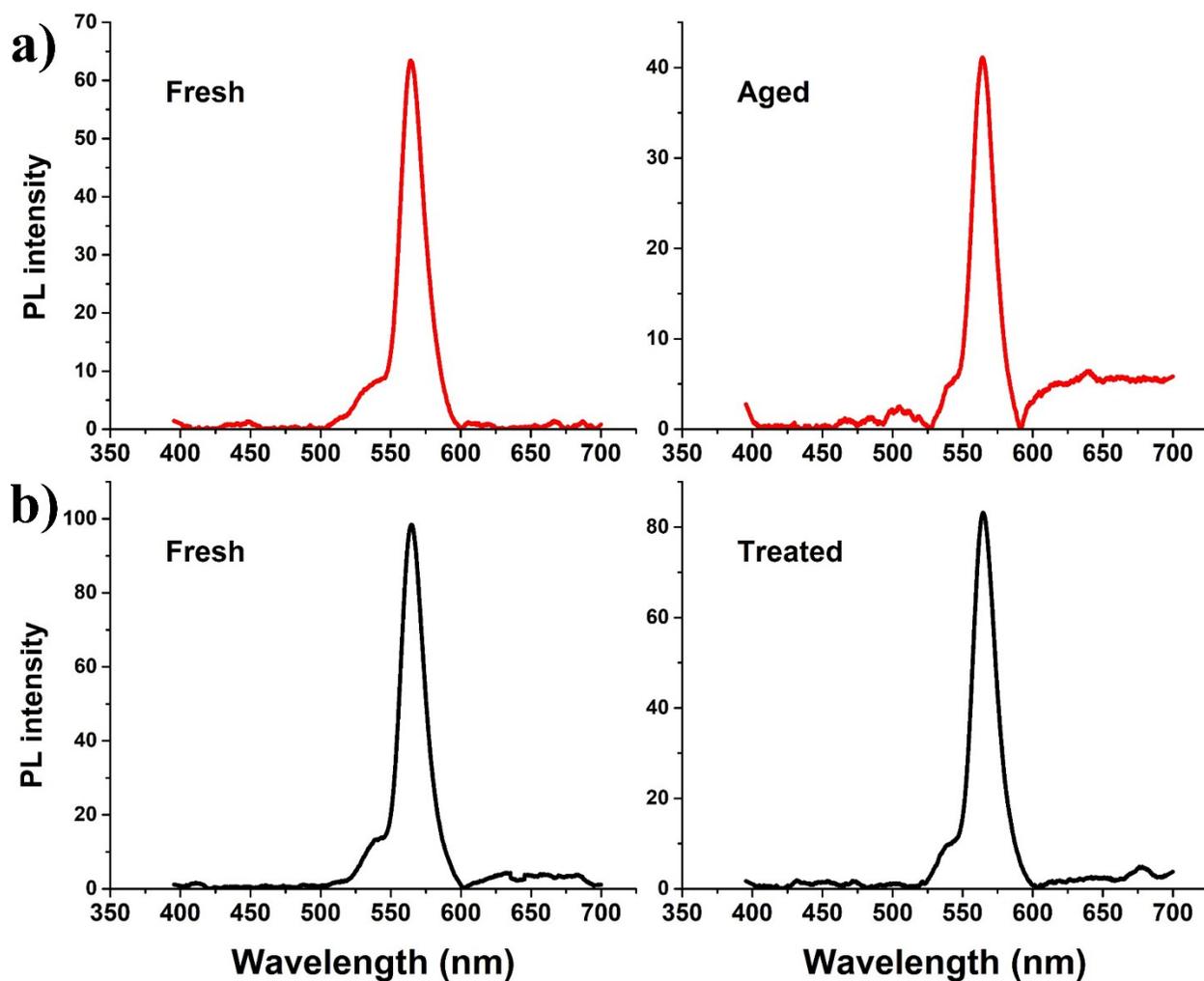
**Figure S1** SEM images of the as-prepared Pb(OH)Br crystals dispersed on the glass substrate.



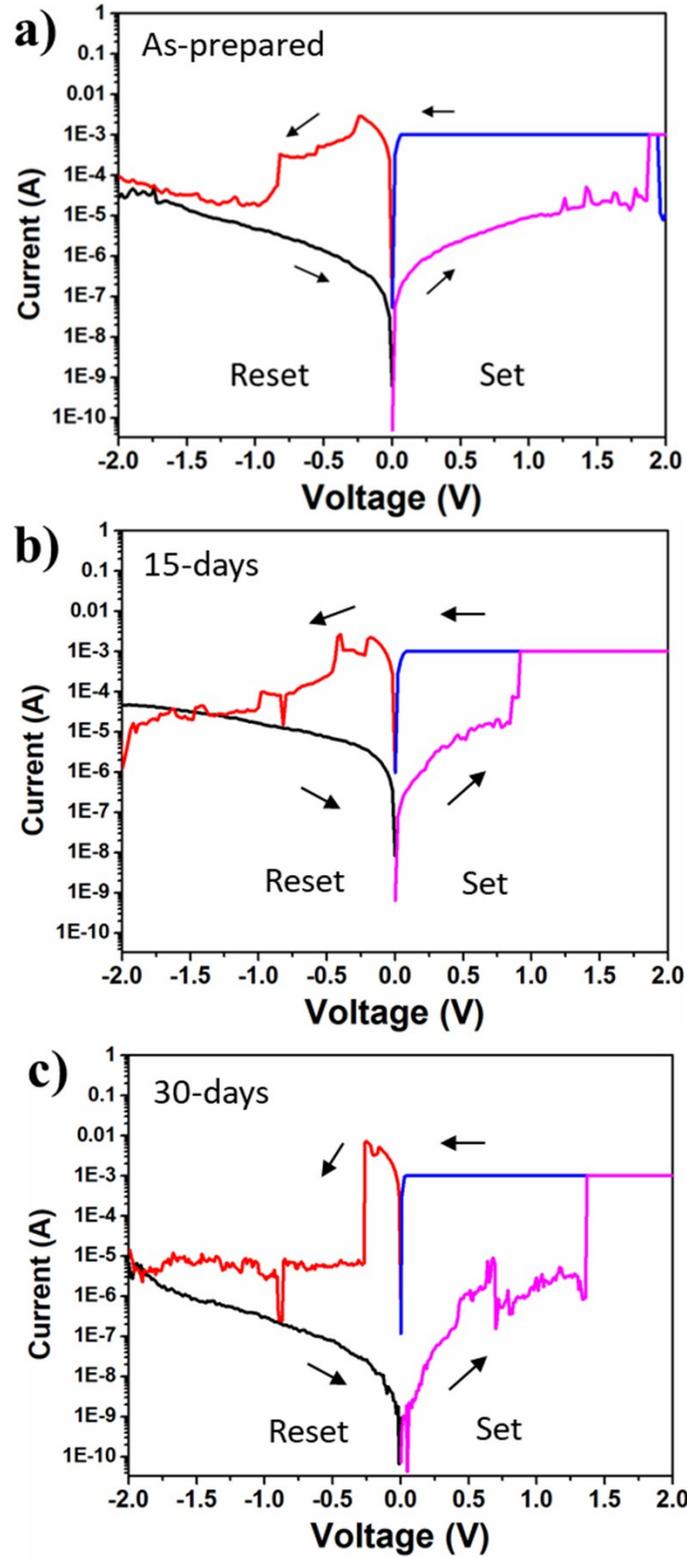
**Figure S2** SEM images of the as-prepared MAPbBr<sub>3</sub> crystals and the corresponding size distribution histogram.



**Figure S3** EDS analysis of the MAPbBr<sub>3</sub> perovskites.



**Figure S4** (a) PL spectra of the as-prepared MAPbBr<sub>3</sub> and after being exposed to a humid environment with a relative humidity of 60±10% for 40 days. (b) PL spectra of the as-prepared MAPbBr<sub>3</sub> and thermally treated at 90 °C for 60 h.



**Figure S5** I-V characteristics of the as-prepared and the aged ReRAM device. (a) As-prepared. (b) Aged for 15 days. (c) Aged for 30 days.